

Title of Change:	Wafer Capacity Expansion for Trench 3 Schottky MOSFETs					
Proposed first ship date:	28 August 2015					
Contact information:	Contact your local ON Semiconductor Sales Office or Melyssa Hutchins <melyssa.hutchins@onsemi.com></melyssa.hutchins@onsemi.com>					
Samples:	Contact your local ON Semiconductor Sales Office or Brian Goodburn <brian.goodburn@onsemi.com></brian.goodburn@onsemi.com>					
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or Donna Scheuch <d.scheuch@onsemi.com></d.scheuch@onsemi.com>					
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>					
Change Part Identification:	There will be change to the finished good part marking on product assembled with the Trench Die fabricated from the UMC Wafer Fab facility. Full traceability of the die manufacturing facility will be available through the lot number recorded on the shipping labels.					
Change category(s): Wafer Fab Change Ssembly Change Test Change	 Product specific change Manufacturing Site Change/Addition Datasheet/Product Doc change Manufacturing Process Change Shipping/Packaging/Marking Material Change Other: 					
Sites Affected: All site(s) not applicable ON Semiconductor site(s) : External Foundry/Subcon site						
Description and Purpose:						

This Product Change Notice is to announce that ON Semiconductor is adding wafer fabrication capacity for their Trench 3 schottky MOSFET technology silicon platforms. ON Semiconductor has qualified United Microelectronics Corp (UMC), a wafer fabrication facility located in Taiwan. Upon expiration of this FPCN, ON Semiconductor will supply parts utilizing the UMC fab. Device quality and reliability will continue to meet ON Semiconductors high standards.



Test	Name	Test Conditions	Test Results	(rej/ ss)	(rej/ ss)	(rej/ ss)	(rej/ ss)
			Read Point	NTMFS4933	NTMFS4933	NTMFS4935	NTMFS4935
Prep	Sample preparation and initial part testing	various	Initial Electrical	done	done	done	done
HTRB	High Temp Reverse Bias	TA = 150°C , Vgss = 100% of max rated	504 Hrs	0/77	0/77	0/77	0/77
HTGB	High Temp Gate Bias	TA = 150°C , Vdss = 80% of max rated	504 Hrs	0/77	0/77	0/77	0/77
MSL 1 PC - IOL	Intermittent Operating Life + PC	Ta=+25°C, delta Tj=100°C On/of = 2 min	7500 Hrs	0/77	0/77	0/77	0/77
MSL 1 PC - TC	Temperature Cycling + PC	-55 °C to + 150°C	500 Cyc	0/77	0/77	0/77	0/77
MSL 1 PC - AC	Autoclave + PC	121°C/100% RH/15psig	96 Hrs	0/77	0/77	0/77	0/77
MSL 1 PC - HAST	Highly Accelerated Stress Test	Temp= +131°C, RH=85% , p = 18.8 psig, bias	96 Hrs	0/77	0/77	0/77	0/77

Test	Name	Test Conditions	End Point Req's	Test Results	(rej/ ss)	(rej/ ss)	(rej/ ss)	(rej/ ss)
				Read Point	Lot A NTMFS4982NF	Lot B NTMFS4982NF	Lot C NTMFS4982NF	NTMFS4982NF Control
Prep	Sample preparation and initial part testing	various		Initial Electrical	done	done	done	done
HTRB	High Temp Reverse Bias	Tj = 150°C for 1008 hours	c = 0, Room	168 hr	0/84	0/84	0/84	0/84
				504 Hrs	0/84	0/84	0/84	0/84
				1008 Hrs	0/84	0/84	0/84	0/84

Electrical Characteristic Summary:

There is no change in electrical parametric performance. Characterization data is available upon request.

List of affected Standard Parts:

NTMFD4901NFT1G NTMFD4902NFT1G NTMFS4982NFT1G NTMFS4983NFT1G NTMFS4985NFT1G NTMFS4985NFT3G